## 2N3906

## General Purpose Transistors

PNP Silicon

## Features

- $\mathrm{Pb}-$ Free Packages are Available*


## MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Collector - Emitter Voltage | $\mathrm{V}_{\mathrm{CEO}}$ | 40 | Vdc |
| Collector - Base Voltage | $\mathrm{V}_{\mathrm{CBO}}$ | 40 | Vdc |
| Emitter - Base Voltage | $\mathrm{V}_{\text {EBO }}$ | 5.0 | Vdc |
| Collector Current - Continuous | $\mathrm{I}_{\mathrm{C}}$ | 200 | mAdc |
| Total Device Dissipation $@ \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ <br> Derate above $25^{\circ} \mathrm{C}$ | $\mathrm{P}_{\mathrm{D}}$ | 625 | mW |
| $\mathrm{~mW} /{ }^{\circ} \mathrm{C}$ |  |  |  |
| Total Power Dissipation @ $\mathrm{T}_{\mathrm{A}}=60^{\circ} \mathrm{C}$ | $\mathrm{P}_{\mathrm{D}}$ | 250 | mW |
| Total Device Dissipation @ $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ <br> Derate above $25^{\circ} \mathrm{C}$ | $\mathrm{P}_{\mathrm{D}}$ | 1.5 | W <br> $\mathrm{mW} /{ }^{\circ} \mathrm{C}$ |
| Operating and Storage Junction <br> Temperature Range | $\mathrm{T}_{\mathrm{J}}, \mathrm{T}_{\text {stg }}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

THERMAL CHARACTERISTICS (Note 1)

| Characteristic | Symbol | Max | Unit |
| :--- | :---: | :---: | :---: |
| Thermal Resistance, Junction-to-Ambient | $\mathrm{R}_{\text {өJA }}$ | 200 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Thermal Resistance, Junction-to-Case | $\mathrm{R}_{\text {өJC }}$ | 83.3 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates Data in addition to JEDEC Requirements.
[^0]ON Semiconductor ${ }^{\circledR}$

## http://onsemi.com

TO-92
CASE 29
STYLE 1

## MARKING DIAGRAM



| A | $=$ Assembly Location |
| :--- | :--- |
| L | $=$ Wafer Lot |
| Y | $=$ Year |
| W | $=$ Work Week |
| - | $=$ Pb-Free Package |

(Note: Microdot may be in either location)

ORDERING INFORMATION
See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

ELECTRICAL CHARACTERISTICS $\left(\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)

| Characteristic |  | Symbol | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS |  |  |  |  |  |
| Collector-Emitter Breakdown Voltage (Note 2) | $\left(\mathrm{I}_{\mathrm{C}}=1.0 \mathrm{mAdc}, \mathrm{I}_{\mathrm{B}}=0\right)$ | $\mathrm{V}_{\text {(BR) }}$ CEO | 40 | - | Vdc |
| Collector-Base Breakdown Voltage | $\left(\mathrm{I}_{\mathrm{C}}=10 \mu \mathrm{Adc}, \mathrm{I}_{\mathrm{E}}=0\right.$ ) | $\mathrm{V}_{\text {(BR) }} \mathrm{VBO}$ | 40 | - | Vdc |
| Emitter-Base Breakdown Voltage | $\left(\mathrm{I}_{\mathrm{E}}=10 \mu \mathrm{Adc}, \mathrm{I}_{\mathrm{C}}=0\right)$ | $\mathrm{V}_{\text {(BR) }{ }^{\text {ebo }}}$ | 5.0 | - | Vdc |
| Base Cutoff Current | $\left(\mathrm{V}_{\text {CE }}=30 \mathrm{Vdc}, \mathrm{V}_{\text {EB }}=3.0 \mathrm{Vdc}\right)$ | $\mathrm{I}_{\mathrm{BL}}$ | - | 50 | nAdc |
| Collector Cutoff Current | $\left(\mathrm{V}_{\text {CE }}=30 \mathrm{Vdc}, \mathrm{V}_{\text {EB }}=3.0 \mathrm{Vdc}\right)$ | $I_{\text {CEX }}$ | - | 50 | nAdc |

ON CHARACTERISTICS (Note 2)

| DC Current Gain | $\begin{gathered} \left(\mathrm{I}_{\mathrm{C}}=0.1 \mathrm{mAdc}, \mathrm{~V}_{\mathrm{CE}}=1.0 \mathrm{Vdc}\right) \\ \left(\mathrm{I}_{\mathrm{C}}=1.0 \mathrm{mAdc}, \mathrm{~V}_{\mathrm{CE}}=1.0 \mathrm{Vdc}\right) \\ \left(\mathrm{I} \mathrm{C}=10 \mathrm{mAdc}, \mathrm{~V}_{\mathrm{CE}}=1.0 \mathrm{Vdc}\right) \\ \left(\mathrm{I}_{\mathrm{C}}=50 \mathrm{mAdc}, \mathrm{~V}_{\mathrm{CE}}=1.0 \mathrm{Vdc}\right) \\ \left(\mathrm{I}_{\mathrm{C}}=100 \mathrm{mAc}, \mathrm{~V}_{\mathrm{CE}}=1.0 \mathrm{Vdc}\right) \end{gathered}$ | $\mathrm{h}_{\text {FE }}$ | $\begin{gathered} 60 \\ 80 \\ 100 \\ 60 \\ 30 \end{gathered}$ | $\begin{gathered} - \\ - \\ 300 \\ - \\ - \end{gathered}$ | - |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Collector-Emitter Saturation Voltage | $\begin{aligned} & \left(\mathrm{I}_{\mathrm{C}}=10 \mathrm{mAdc}, \mathrm{I}_{\mathrm{B}}=1.0 \mathrm{mAdc}\right) \\ & \left(\mathrm{I}_{\mathrm{C}}=50 \mathrm{mAdc}, \mathrm{I}_{\mathrm{B}}=5.0 \mathrm{mAdc}\right. \end{aligned}$ | $\mathrm{V}_{\text {CE(sat) }}$ | - | $\begin{gathered} 0.25 \\ 0.4 \end{gathered}$ | Vdc |
| Base-Emitter Saturation Voltage | ( $\mathrm{I}_{\mathrm{C}}=10 \mathrm{mAdc}, \mathrm{I}_{\mathrm{B}}=1.0 \mathrm{mAdc}$ ) $\left(I_{C}=50 \mathrm{mAdc}, \mathrm{I}_{\mathrm{B}}=5.0 \mathrm{mAdc}\right)$ | $V_{B E \text { (sat) }}$ | $0.65$ | $\begin{aligned} & 0.85 \\ & 0.95 \end{aligned}$ | Vdc |

SMALL-SIGNAL CHARACTERISTICS

| Current-Gain - Bandwidth Product | $\left(\mathrm{l}_{\mathrm{C}}=10 \mathrm{mAdc}, \mathrm{V}_{\mathrm{CE}}=20 \mathrm{Vdc}, \mathrm{f}=100 \mathrm{MHz}\right.$ ) | $\mathrm{f}_{\mathrm{T}}$ | 250 | - | MHz |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Output Capacitance | $\left(\mathrm{V}_{C B}=5.0 \mathrm{Vdc}, \mathrm{I}_{\mathrm{E}}=0, \mathrm{f}=1.0 \mathrm{MHz}\right)$ | Cobo | - | 4.5 | pF |
| Input Capacitance | $\left(\mathrm{V}_{\text {EB }}=0.5 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=0, \mathrm{f}=1.0 \mathrm{MHz}\right)$ | $\mathrm{C}_{\text {ibo }}$ | - | 10 | pF |
| Input Impedance | $\left(\mathrm{I}_{\mathrm{C}}=1.0 \mathrm{mAdc}, \mathrm{V}_{\text {CE }}=10 \mathrm{Vdc}, \mathrm{f}=1.0 \mathrm{kHz}\right.$ ) | $\mathrm{h}_{\text {ie }}$ | 2.0 | 12 | $\mathrm{k} \Omega$ |
| Voltage Feedback Ratio | $\left(\mathrm{I}_{\mathrm{C}}=1.0 \mathrm{mAdc}, \mathrm{V}_{\mathrm{CE}}=10 \mathrm{Vdc}, \mathrm{f}=1.0 \mathrm{kHz}\right.$ ) | $\mathrm{h}_{\mathrm{re}}$ | 0.1 | 10 | X $10^{-4}$ |
| Small-Signal Current Gain | $\left(\mathrm{I}_{\mathrm{C}}=1.0 \mathrm{mAdc}, \mathrm{V}_{\mathrm{CE}}=10 \mathrm{Vdc}, \mathrm{f}=1.0 \mathrm{kHz}\right.$ ) | $\mathrm{h}_{\mathrm{fe}}$ | 100 | 400 | - |
| Output Admittance | ( $\mathrm{IC}_{\mathrm{C}}=1.0 \mathrm{mAdc}, \mathrm{V}_{\mathrm{CE}}=10 \mathrm{Vdc}, \mathrm{f}=1.0 \mathrm{kHz}$ ) | $\mathrm{h}_{\text {oe }}$ | 3.0 | 60 | $\mu \mathrm{mhos}$ |
| Noise Figure ( $\mathrm{IC}_{\mathrm{C}}=1$ | $\mathrm{dc}, \mathrm{V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}, \mathrm{R}_{\mathrm{S}}=1.0 \mathrm{k} \Omega, \mathrm{f}=1.0 \mathrm{kHz}$ ) | NF | - | 4.0 | dB |

## SWITCHING CHARACTERISTICS

| Delay Time | $\left(\mathrm{V}_{\mathrm{CC}}=3.0 \mathrm{Vdc}, \mathrm{V}_{\mathrm{BE}}=0.5 \mathrm{Vdc}\right.$, $\left.\mathrm{I}_{\mathrm{C}}=10 \mathrm{mAdc}, \mathrm{I}_{\mathrm{B} 1}=1.0 \mathrm{mAdc}\right)$ | $\mathrm{t}_{\mathrm{d}}$ | - | 35 | ns |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Rise Time |  | $\mathrm{t}_{\mathrm{r}}$ | - | 35 | ns |
| Storage Time | $\left(\mathrm{V}_{\mathrm{CC}}=3.0 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=10 \mathrm{mAdc}, \mathrm{I}_{\mathrm{B} 1}=\mathrm{I}_{\mathrm{B} 2}=1.0 \mathrm{mAdc}\right)$ | $\mathrm{t}_{\text {s }}$ | - | 225 | ns |
| Fall Time | $\left(\mathrm{V}_{\mathrm{CC}}=3.0 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=10 \mathrm{mAdc}, \mathrm{I}_{\mathrm{B} 1}=\mathrm{I}_{\mathrm{B} 2}=1.0 \mathrm{mAdc}\right)$ | $\mathrm{t}_{\mathrm{f}}$ | - | 75 | ns |

2. Pulse Test: Pulse Width $\leq 300 \mu \mathrm{~s}$; Duty Cycle $\leq 2 \%$.

## 2N3906

ORDERING INFORMATION

| Device | Package | Shipping ${ }^{\dagger}$ |
| :---: | :---: | :---: |
| 2N3906 | TO-92 | 5000 Units / Bulk |
| 2N3906G | $\begin{gathered} \text { TO-92 } \\ \text { (Pb-Free) } \end{gathered}$ | 5000 Units / Bulk |
| 2N3906RL1 | TO-92 | 2000 / Tape \& Reel |
| 2N3906RL1G | $\begin{gathered} \text { TO-92 } \\ \text { (Pb-Free) } \end{gathered}$ | 2000 / Tape \& Reel |
| 2N3906RLRA | TO-92 | 2000 / Tape \& Reel |
| 2N3906RLRAG | $\begin{gathered} \text { TO-92 } \\ \text { (Pb-Free) } \end{gathered}$ | 2000 / Tape \& Reel |
| 2N3906RLRM | TO-92 | 2000 / Tape \& Ammo Box |
| 2N3906RLRMG | $\begin{gathered} \text { TO-92 } \\ \text { (Pb-Free) } \end{gathered}$ | 2000 / Tape \& Ammo Box |
| 2N3906RLRP | TO-92 | 2000 / Tape \& Ammo Box |
| 2N3906RLRPG | $\begin{gathered} \text { TO-92 } \\ \text { (Pb-Free) } \end{gathered}$ | 2000 / Tape \& Ammo Box |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.


* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit


Figure 2. Storage and Fall Time Equivalent Test Circuit

## TYPICAL TRANSIENT CHARACTERISTICS



Figure 3. Capacitance


Figure 5. Turn-On Time


Figure 6. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS
$\left(\mathrm{V}_{\mathrm{CE}}=-5.0 \mathrm{Vdc}, \mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}\right.$, Bandwidth $\left.=1.0 \mathrm{~Hz}\right)$


Figure 7.


Figure 8.
h PARAMETERS
$\left(\mathrm{V}_{\mathrm{CE}}=-10 \mathrm{Vdc}, \mathrm{f}=1.0 \mathrm{kHz}, \mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}\right)$


Figure 9. Current Gain


Figure 11. Input Impedance


Figure 10. Output Admittance


Figure 12. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS


Figure 13. DC Current Gain


Figure 14. Collector Saturation Region


Figure 15. "ON" Voltages


Figure 16. Temperature Coefficients


STRAIGHT LEAD BULK PACK


BENT LEAD TAPE \& REEL AMMO PACK

 BULK PACK


BENT LEAD TAPE \& REEL AMMO PACK


TO-92 (TO-226)
CASE 29-11
ISSUE AM
DATE 09 MAR 2007

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: INCH
2. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
3. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

| DIM | INCHES |  | MILLIMETERS |  |
| :---: | ---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
| A | 0.175 | 0.205 | 4.45 | 5.20 |
| B | 0.170 | 0.210 | 4.32 | 5.33 |
| C | 0.125 | 0.165 | 3.18 | 4.19 |
| D | 0.016 | 0.021 | 0.407 | 0.533 |
| G | 0.045 | 0.055 | 1.15 | 1.39 |
| H | 0.095 | 0.105 | 2.42 | 2.66 |
| J | 0.015 | 0.020 | 0.39 | 0.50 |
| K | 0.500 | --- | 12.70 | --- |
| L | 0.250 | --- | 6.35 | --- |
| N | 0.080 | 0.105 | 2.04 | 2.66 |
| P | --- | 0.100 | --- | 2.54 |
| R | 0.115 | --- | 2.93 | --- |
| V | 0.135 | --- | 3.43 | --- |

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. . LEAD DIMENSION IS UNCONTROLLED I

|  | MILLIMETERS |  |
| :---: | ---: | ---: |
| DIM | MIN | MAX |
| A | 4.45 | 5.20 |
| B | 4.32 | 5.33 |
| C | 3.18 | 4.19 |
| D | 0.40 | 0.54 |
| G | 2.40 | 2.80 |
| J | 0.39 | 0.50 |
| K | 12.70 | --- |
| N | 2.04 | 2.66 |
| P | 1.50 | 4.00 |
| R | 2.93 | --- |
| V | 3.43 | --- |

STYLES ON PAGE 2

| DOCUMENT NUMBER: | 98ASB42022B | Electronic versions are uncontrolled except when <br> accessed directly from the Document Repository. Printed <br> versions are uncontrolled except when stamped <br> "CONTROLLED COPY" in red. |  |
| ---: | :--- | :--- | :--- |
| STATUS: | ON SEMICONDUCTOR STANDARD |  |  |
| NEW STANDARD: |  |  | PAGE 1 OF 3 |


| STYLE 1: <br> PIN 1. | EMITTER | STYLE 2: <br> PIN 1. | BASE | STYLE 3: PIN 1. | ANODE | STYLE 4: PIN 1. | CATHODE | STYLE 5: PIN 1. | DRAIN |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 2. | BASE | 2. | EMITTER |  | ANODE | 2. | CATHODE | 2. | SOURCE |
| 3. | COLLECTOR | 3. | COLLECTOR | 3. | CATHODE | 3. | ANODE | 3. | GATE |
| STYLE 6: |  | STYLE 7: |  | STYLE 8: |  | STYLE 9: |  | STYLE 10: |  |
| PIN 1. | GATE | PIN 1. | SOURCE | PIN 1. | DRAIN | PIN 1. | BASE 1 | PIN 1. | CATHODE |
| 2. | SOURCE \& SUBSTRATE | 2. | DRAIN | 2. | GATE | 2. | EMITTER | 2. | GATE |
| 3. | DRAIN | 3. | GATE | 3. | SOURCE \& SUBSTRATE | 3. | BASE 2 | 3. | ANODE |
| STYLE 11: |  | STYLE 12: |  | STYLE 13: |  | STYLE 14: |  | STYLE 15: |  |
| PIN 1. | ANODE | PIN 1. | MAIN TERMINAL 1 | PIN 1. | ANODE 1 | PIN 1. | EMITTER | PIN 1. | ANODE 1 |
| 2. | CATHODE \& ANODE | 2. | GATE | 2. | GATE | 2. | COLLECTOR | 2. | CATHODE |
| 3. | CATHODE | 3. | MAIN TERMINAL 2 | 3. | CATHODE 2 | 3. | BASE | 3. | ANODE 2 |
| STYLE 16: |  | STYLE 17: |  | STYLE 18: |  | STYLE 19: |  | STYLE 20: |  |
| PIN 1. | ANODE | PIN 1. | COLLECTOR | PIN 1. | ANODE | PIN 1. | GATE | PIN 1. | NOT CONNECTED |
| 2. | GATE | 2. | BASE | 2. | CATHODE | 2. | ANODE | 2. | CATHODE |
| 3. | CATHODE | 3. | EMITTER | 3. | NOT CONNECTED | 3. | CATHODE | 3. | ANODE |
| STYLE 21: |  | STYLE 22: |  | STYLE 23: |  | STYLE 24: |  | STYLE 25: |  |
| PIN 1. | COLLECTOR | PIN 1. | SOURCE | PIN 1. | GATE | PIN 1. | EMITTER | PIN 1. | MT 1 |
|  | EMITTER | 2. | GATE | 2. | SOURCE | 2. | COLLECTOR/ANODE | 2. | GATE |
|  | BASE | 3. | DRAIN | 3. | DRAIN | 3. | CATHODE | 3. | MT 2 |
| STYLE 26: |  | STYLE 27: |  | STYLE 28: |  | STYLE 29: |  | STYLE 30: |  |
| PIN 1. | $V_{C C}$ | PIN 1. | MT | PIN 1. | CATHODE | PIN 1. | NOT CONNECTED | PIN 1. | DRAIN |
| 2. | GROUND 2 | 2. | SUBSTRATE | 2. | ANODE | 2. | ANODE | 2. | GATE |
|  | OUTPUT | 3. | MT | 3. | GATE | 3. | CATHODE | 3. | SOURCE |
| STYLE 31: |  | STYLE 32: |  | STYLE 33: |  | STYLE 34: |  | STYLE 35: |  |
| PIN 1. | GATE | PIN 1. | BASE | PIN 1. | RETURN | PIN 1. | INPUT | PIN 1. | GATE |
| 2. | DRAIN | 2. | COLLECTOR | 2. | INPUT | 2. | GROUND | 2. | COLLECTOR |
| 3. | SOURCE | 3. | EMITTER | 3. | OUTPUT | 3. | LOGIC | 3. | EMITTER |


| DOCUMENT NUMBER: | 98ASB42022B |
| ---: | :--- |
| STATUS: | ON SEMICONDUCTOR STANDARD |
| NEW STANDARD: |  |
| DESCRIPTION: | TO-92 (TO-226) |

Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.


ON Semiconductor and (ON) are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should
Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.
onsemi, OnSemi., and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that onsemi was negligent regarding the design or manufacture of the part. onsemi is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

## LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com
onsemi Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1800-282-9855 Toll Free USA/Canada
Phone: 011421337902910

Europe, Middle East and Africa Technical Support:
Phone: 00421337902910
For additional information, please contact your local Sales Representative

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components
Click to view similar products for Bipolar Transistors - BJT category:
Click to view products by ON Semiconductor manufacturer:
Other Similar products are found below :
619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE158 NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMMTA92QTA 2N2369ADCSM 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E US6T6TR 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E UMX21NTR EMT2T2R MCH6102-TL-E FP204-TL-E NJL0302DG 2N3583 2SA1434-TB-E 2SC3143-4-TB-E 2SD1621S-TD-E NTE103 30A02MH-TL-E NSV40301MZ4T1G NTE101 NTE13 NTE15 NTE16001


[^0]:    *For additional information on our $\mathrm{Pb}-$ Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

